

High Power LED chip 2500 A.

High Power

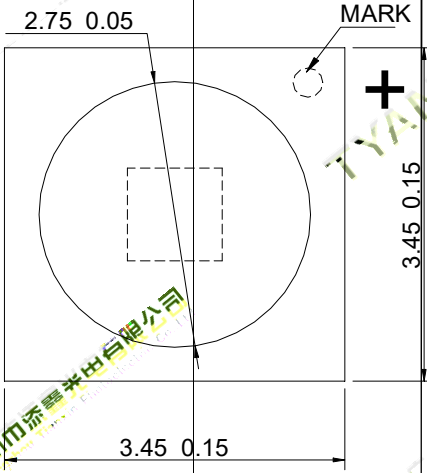
UV

Capacitor

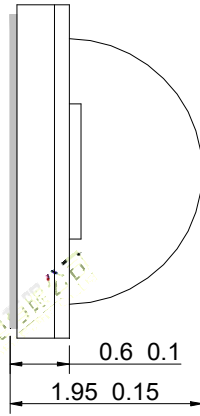
GaN

GaN

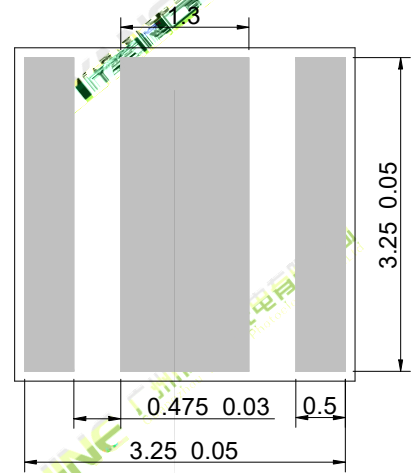
Aluminum nitride
Aluminum nitride
Aluminum nitride



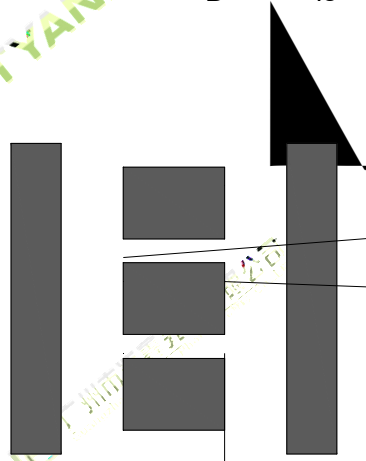
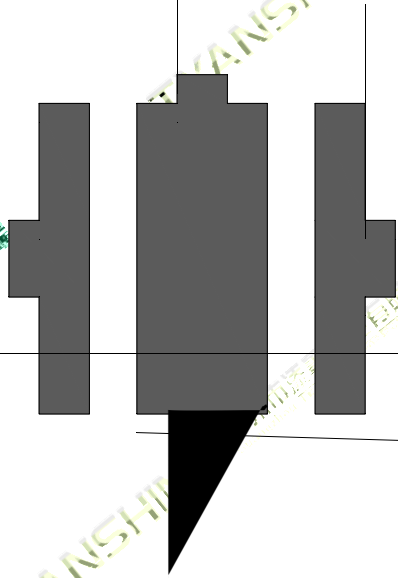
T ie



Side ie

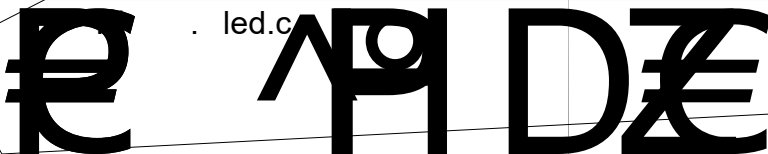


B ie



e

e



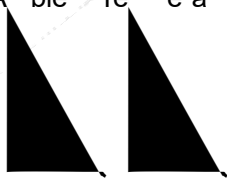
F adC e	IF	2500	A
Re e eV l age	V _R	N de ig ed f e e e e a i	V
P e Di i ai	P _D	9.5	W
J ci Te e a e	T _j	150	
Elec a ic Di cha ge The h ld (ESD)	ESD	ESD e ii e de ice	V
S age Te e a e	T _g	-40 +70	
O e ai Te e a e	T	-30 +85	

1. Specific a e bjec cha ge i h ice.
2. The da a hi ecifica i i f efe e ce l a d he ac al da a i i acc da ce i h he ack ledg e .
3. P eca i f ESD:
 STATIC SH D Elec ic i a d ge da age he LED. I i ec e ded e a i ba d a i-elec gl e he ha dli g he LED. All de ice , e i a d achi e be e l g ded.

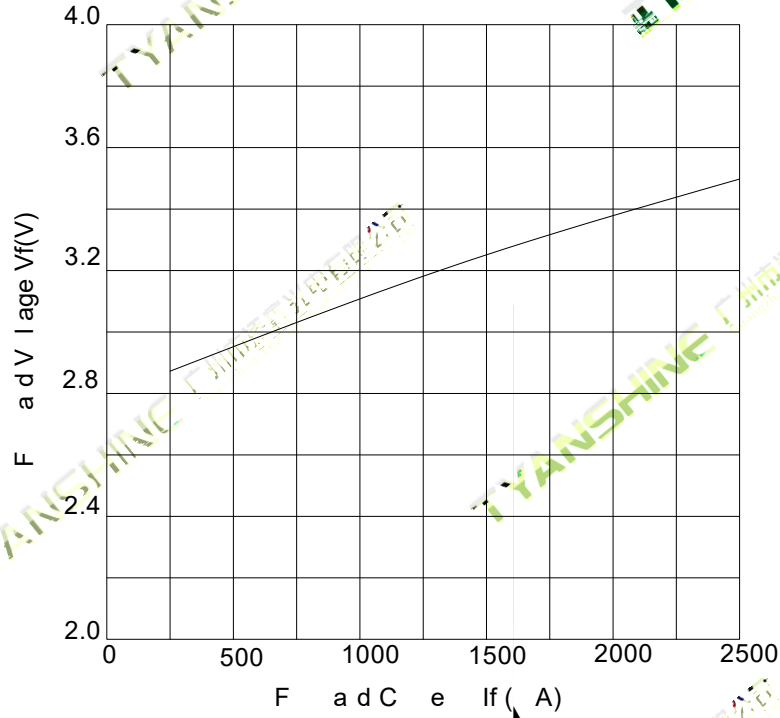
L i F l				270	300	330
F a d V l a g e	V _f			2.8	3.1	3.4
Vie i g A g l e a 50 IV	2 1/2	If=1000 A			120	
Peak E i i Wa e l e g h				518	523	528
D i a Wa e l e g h	d			525	530	535
Vie i g A g l e a 50 IV	2 1/2			28	33	38
Re e e C e	I _R					A
The al Re i a c e J c i C a e	R _{jc}				4.9	K/W
Te e a e C e f f i c i e n t V l a g e	V _{F/T}	If=1000 A			-2	V/

- 1.L i i e i i e a e d i h a l i g h e a d f i l e c b i a i h a a i a e h e C I E e e e c e .
2. 1/2 the ff-a i a g l e w h i c h h e l i i e i i h a l f h e a i i e i .
- 3.L f l e a e l e a c e 15%.
- 4.F a d l a g e a e e l e a 10%V.

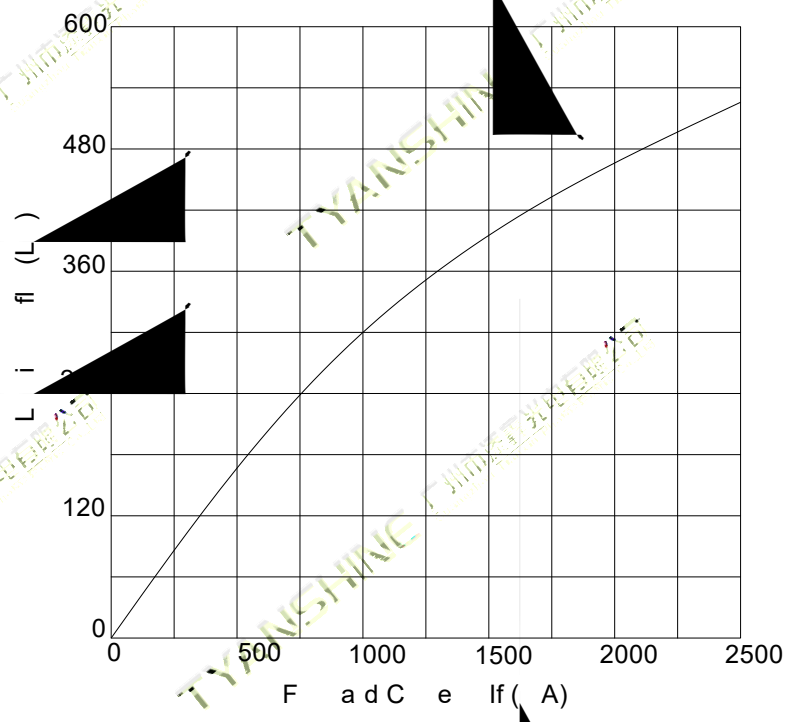
(25) Absolute Temperature Coefficient



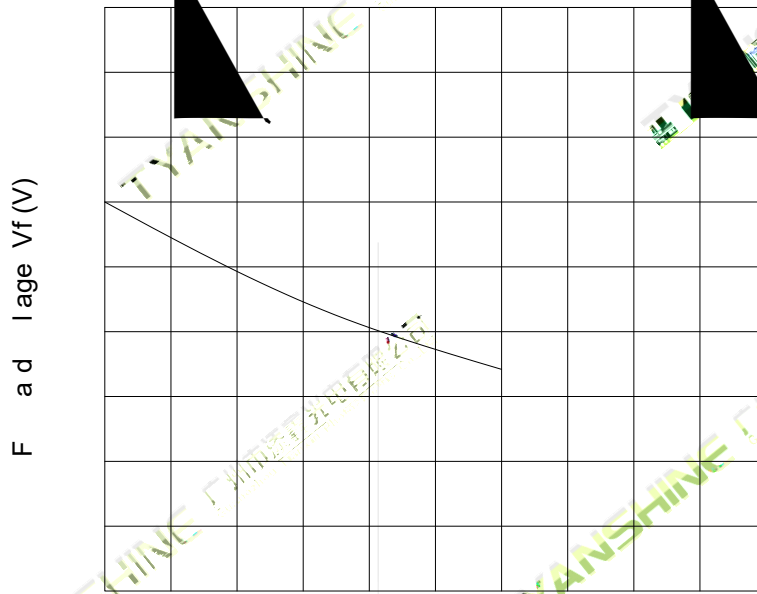
Forward Current VS. Forward Voltage



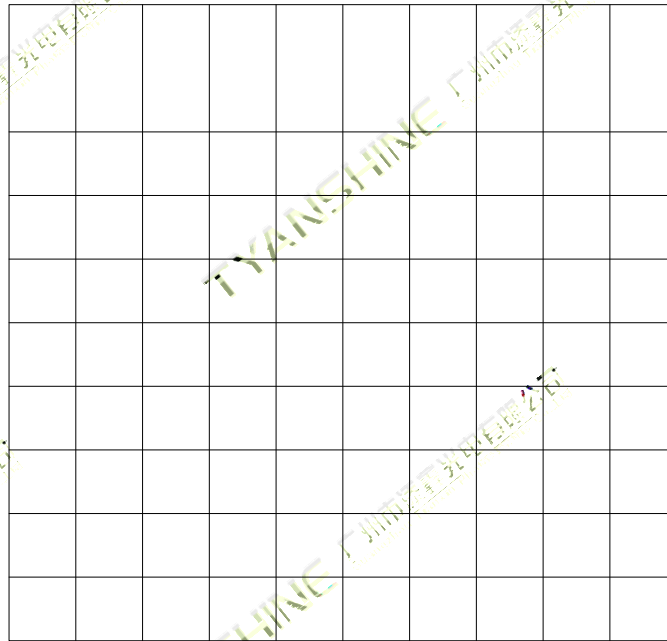
Forward Current VS. Light Intensity



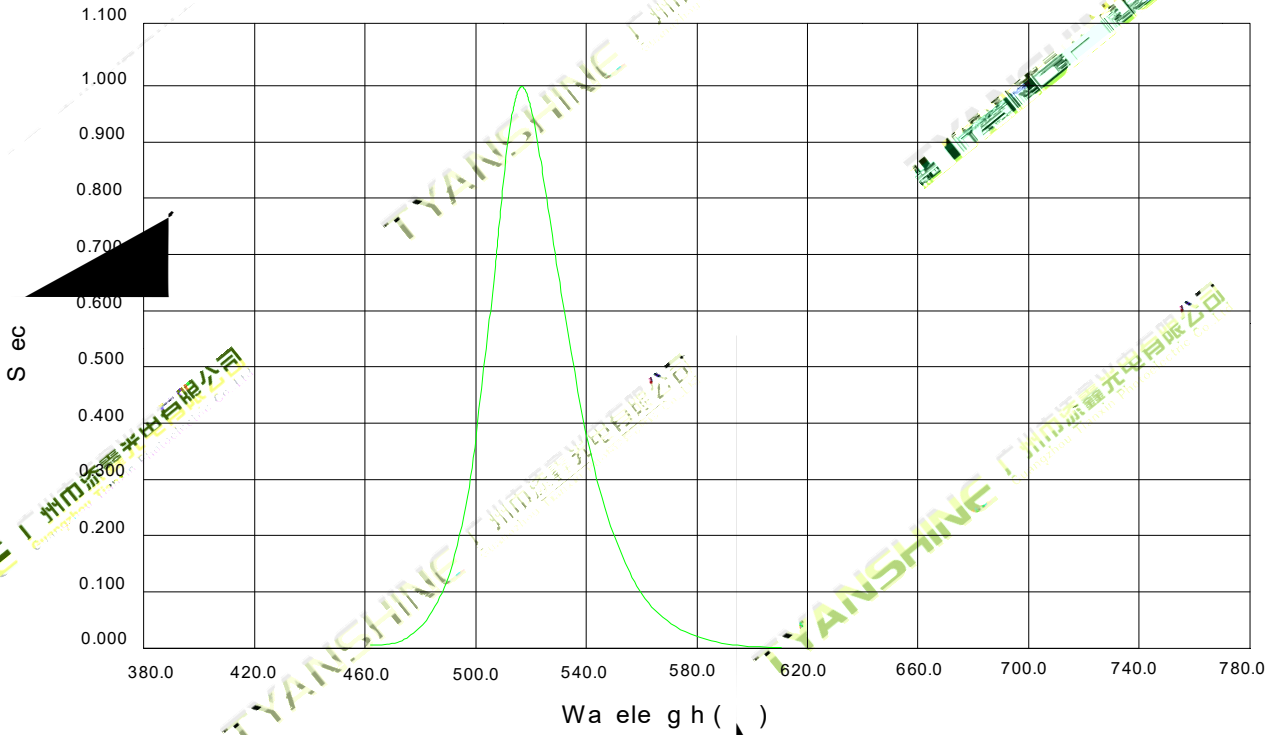
Temperature VS. Forward Voltage (IF=1000 mA)



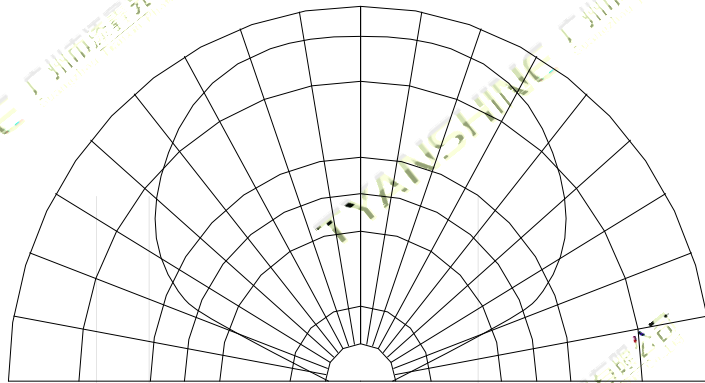
Temperature ()



Relative Spectral Distribution



Beam Pattern



Relative Intensity (LOP@MAX=1)

1.2 1/2 degree half angle
2. Viewing angle less than 5 degrees

